

# **BGD704**

# 750 MHz, 20 dB gain power doubler amplifier

Rev. 8 — 28 September 2010

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Hybrid amplifier module in a SOT115J package operating with a voltage supply of 24 V (DC).

### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

### 1.2 Features and benefits

- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability

# 1.3 Applications

■ CATV systems in the frequency range of 40 MHz to 750 MHz

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz	19.5	20	20.5	dB
		f = 750 MHz	20	21	-	dB
I <sub>tot</sub>	total current consumption (DC)	V <sub>B</sub> = 24 V	-	425	435	mΑ



### 750 MHz, 20 dB gain power doubler amplifier

# 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline Graphic symbol
1	input	
2	common	1 3 5 7 9
3	common	
5	+V <sub>B</sub>	12/3/7/8
7	common	2 3 7 8 sym095
8	common	,
9	output	

# 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BGD704	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J			

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{i}$	RF input voltage		-	65	dBmV
T <sub>stg</sub>	storage temperature		-40	+100	°C
T <sub>mb</sub>	mounting base operating temperature		-20	+100	°C

# 5. Characteristics

Table 5. Characteristics

Bandwidth 40 MHz to 750 MHz;  $V_B = 24$  V;  $T_{mb} = 35$  °C;  $Z_S = Z_L = 75$   $\Omega$ .

Parameter	Conditions	Min	Тур	Max	Unit
power gain	f = 50 MHz	19.5	20	20.5	dB
	f = 750 MHz	20	21	-	dB
slope cable equivalent	f = 40 MHz to 750 MHz	0	1	2	dB
flatness of frequency response	f = 40 MHz to 750 MHz	-	±0.2	±0.5	dB
input return losses	f = 40 MHz to 80 MHz	20	31	-	dB
	f = 80 MHz to 160 MHz	19	29	-	dB
	f = 160 MHz to 320 MHz	18	25	-	dB
	f = 320 MHz to 640 MHz	17	21	-	dB
	f = 640 MHz to 750 MHz	16	21	-	dB
	power gain slope cable equivalent flatness of frequency response	f = 50  MHz $f = 750  MHz$ $slope cable equivalent$ $f = 40  MHz to  750  MHz$ $flatness of frequency response$ $f = 40  MHz to  750  MHz$ $input return losses$ $f = 40  MHz to  80  MHz$ $f = 80  MHz to  160  MHz$ $f = 160  MHz to  320  MHz$ $f = 320  MHz to  640  MHz$	$\begin{array}{c} \text{power gain} & \text{f} = 50 \text{ MHz} & 19.5 \\ \hline f = 750 \text{ MHz} & 20 \\ \\ \text{slope cable equivalent} & \text{f} = 40 \text{ MHz to } 750 \text{ MHz} & 0 \\ \\ \text{flatness of frequency response} & \text{f} = 40 \text{ MHz to } 750 \text{ MHz} & - \\ \\ \text{input return losses} & \text{f} = 40 \text{ MHz to } 80 \text{ MHz} & 20 \\ \hline f = 80 \text{ MHz to } 160 \text{ MHz} & 19 \\ \hline f = 160 \text{ MHz to } 320 \text{ MHz} & 18 \\ \hline f = 320 \text{ MHz to } 640 \text{ MHz} & 17 \\ \hline \end{array}$	power gain       f = 50 MHz       19.5       20         f = 750 MHz       20       21         slope cable equivalent       f = 40 MHz to 750 MHz       0       1         flatness of frequency response input return losses       f = 40 MHz to 750 MHz       -       ±0.2         f = 40 MHz to 80 MHz       20       31         f = 80 MHz to 160 MHz       19       29         f = 160 MHz to 320 MHz       18       25         f = 320 MHz to 640 MHz       17       21	power gain       f = 50 MHz       19.5       20       20.5         f = 750 MHz       20       21       -         slope cable equivalent       f = 40 MHz to 750 MHz       0       1       2         flatness of frequency response       f = 40 MHz to 750 MHz       -       ±0.2       ±0.5         input return losses       f = 40 MHz to 80 MHz       20       31       -         f = 80 MHz to 160 MHz       19       29       -         f = 160 MHz to 320 MHz       18       25       -         f = 320 MHz to 640 MHz       17       21       -

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### 750 MHz, 20 dB gain power doubler amplifier

 Table 5.
 Characteristics ...continued

Bandwidth 40 MHz to 750 MHz;  $V_B = 24$  V;  $T_{mb} = 35$  °C;  $Z_S = Z_L = 75 \Omega$ .

Symbol	Parameter	Conditions	N	1in	Тур	Max	Unit
s <sub>22</sub>	output return losses	f = 40 MHz to 80 MHz	2	0	26	-	dB
		f = 80 MHz to 160 MHz	1:	9	27	-	dB
		f = 160 MHz to 320 MHz	1	8	26	-	dB
		f = 320 MHz to 640 MHz	1	7	24	-	dB
		f = 640 MHz to 750 MHz	1	6	23	-	dB
s <sub>21</sub>	phase response	f = 50 MHz	_	45	-	+45	deg
СТВ	composite triple beat	110 channels flat; $V_0 = 44 \text{ dBmV}$ ; measured at 745.25 MHz	-		-58	<b>–57</b>	dB
X <sub>mod</sub>	cross modulation	110 channels flat; $V_0 = 44 \text{ dBmV}$ ; measured at 55.25 MHz	-		-63	-61	dB
CSO	composite second order distortion	110 channels flat; $V_0 = 44 \text{ dBmV}$ ; measured at 746.5 MHz	-		-61	-56	dB
$d_2$	second order distortion		<u>[1]</u> -		-75	-66	dB
Vo	output voltage	$d_{im} = -60 \text{ dB}$	[2] 6	0.5	63.5	-	dBmV
F	noise figure	f = 50 MHz	-		4.5	5	dB
		f = 450 MHz	-		-	6.5	dB
		f = 550 MHz	-		-	7	dB
		f = 600 MHz	-		-	7	dB
		f = 750 MHz	-		6.5	8.5	dB
I <sub>tot</sub>	total current consumption (DC)		[3]		425	435	mA

<sup>[1]</sup>  $f_p = 55.25$  MHz;  $V_p = 44$  dBmV;  $f_q = 691.25$  MHz;  $V_q = 44$  dBmV; measured at  $f_p + f_q = 746.5$  MHz.

Table 6. Characteristics

Bandwidth 40 MHz to 600 MHz;  $V_B = 24$  V;  $T_{mb} = 35$  °C;  $Z_S = Z_L = 75 \Omega$ .

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz	19.5	20	20.5	dB
		f = 600 MHz	20	20.7	-	dB
SL	slope cable equivalent	f = 40 MHz to 600 MHz	0	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 600 MHz	-	-	±0.3	dB
s <sub>11</sub>	input return losses	f = 40 MHz to 80 MHz	20	31	-	dB
		f = 80 MHz to 160 MHz	19	29	-	dB
		f = 160 MHz to 320 MHz	18	25	-	dB
		f = 320 MHz to 600 MHz	17	21	-	dB
s <sub>22</sub>	output return losses	f = 40 MHz to 80 MHz	20	26	-	dB
		f = 80 MHz to 160 MHz	19	27	-	dB
		f = 160 MHz to 320 MHz	18	26	-	dB
		f = 320 MHz to 600 MHz	17	24	-	dB
S <sub>21</sub>	phase response	f = 50 MHz	-45	-	+45	deg

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<sup>[2]</sup> Measure according to DIN45004B;  $f_p$  = 740.25 MHz;  $V_p$  =  $V_o$ ;  $f_q$  = 747.25 MHz;  $V_q$  =  $V_o$  - 6 dB;  $f_r$  = 749.25 MHz;  $V_r$  =  $V_o$  - 6 dB; measured at  $f_p$  +  $f_q$  -  $f_r$  = 738.25 MHz.

<sup>[3]</sup> The module normally operates at  $V_B = 24 \text{ V}$ , but is able to withstand supply transients up to 30 V.

### 750 MHz, 20 dB gain power doubler amplifier

 Table 6.
 Characteristics ...continued

Bandwidth 40 MHz to 600 MHz;  $V_B = 24$  V;  $T_{mb} = 35$  °C;  $Z_S = Z_L = 75 \Omega$ .

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
СТВ	composite triple beat	85 channels flat; $V_0$ = 44 dBmV; measured at 595.25 MHz	-	-65	-64	dB
$X_{mod}$	cross modulation	85 channels flat; $V_0$ = 44 dBmV; measured at 55.25 MHz	-	-65	-64	dB
CSO	composite second order distortion	85 channels flat; $V_0$ = 44 dBmV; measured at 596.5 MHz	-	-66	-58	dB
$d_2$	second order distortion		<u>[1]</u> _	-	-68	dB
V <sub>o</sub>	output voltage	$d_{im} = -60 \text{ dB}$	<sup>[2]</sup> 63	-	-	dBmV
F	noise figure	see <u>Table 5</u>	-	-	-	dBmV
I <sub>tot</sub>	total current consumption (DC)		[3]	425	435	mΑ

<sup>[1]</sup>  $f_p = 55.25$  MHz;  $V_p = 44$  dBmV;  $f_q = 541.25$  MHz;  $V_q = 44$  dBmV; measured at  $f_p + f_q = 596.5$  MHz.

Table 7. Characteristics

Bandwidth 40 MHz to 550 MHz;  $V_B = 24$  V;  $T_{mb} = 35$  °C;  $Z_S = Z_L = 75 \Omega$ .

Symbol	Parameter	Conditions	Mir	n Typ	Max	Unit
Gp	power gain	f = 50 MHz	19.	5 20	20.5	dB
		f = 550 MHz	20	20.6	-	dB
SL	slope cable equivalent	f = 40 MHz to 550 MHz	0	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 550 MHz	-	-	±0.3	dB
S <sub>11</sub>	input return losses	f = 40 MHz to 80 MHz	20	31	-	dB
		f = 80 MHz to 160 MHz	19	29	-	dB
		f = 160 MHz to 320 MHz	18	25	-	dB
		f = 320 MHz to 550 MHz	17	21	-	dB
S <sub>22</sub>	output return losses	f = 40 MHz to 80 MHz	20	26	-	dB
		f = 80 MHz to 160 MHz	19	27	-	dB
		f = 160 MHz to 320 MHz	18	26	-	dB
		f = 320 MHz to 550 MHz	17	24	-	dB
S <sub>21</sub>	phase response	f = 50 MHz	-45	5 -	+45	deg
СТВ	composite triple beat	77 channels flat; $V_o$ = 44 dBmV; measured at 547.25 MHz	-	-67	-66	dB
$X_{mod}$	cross modulation	77 channels flat; $V_o$ = 44 dBmV; measured at 55.25 MHz	-	-67	-66	dB
CSO	composite second order distortion	77 channels flat; $V_o$ = 44 dBmV; measured at 548.5 MHz	-	-67	-60	dB
d <sub>2</sub>	second order distortion		[1] -	-	-70	dB
Vo	output voltage	$d_{im} = -60 \text{ dB}$	[ <u>2</u> ] 63.	5 -	-	dBmV
F	noise figure	see <u>Table 5</u>	-	-	-	dB
I <sub>tot</sub>	total current consumption (DC)		[3] _	425	435	mA

<sup>[1]</sup>  $f_p = 55.25$  MHz;  $V_p = 44$  dBmV;  $f_q = 493.25$  MHz;  $V_q = 44$  dBmV; measured at  $f_p + f_q = 548.5$  MHz.

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<sup>[2]</sup> Measured according to DIN45004B;  $f_p$  = 590.25 MHz;  $V_p$  =  $V_o$ ;  $f_q$  = 597.25 MHz;  $V_q$  =  $V_o$  - 6 dB;  $f_r$  = 599.25 MHz;  $V_r$  =  $V_o$  - 6 dB; measured at  $f_p$  +  $f_q$  -  $f_r$  = 588.25 MHz.

<sup>[3]</sup> The module normally operates at  $V_B = 24 \text{ V}$ , but is able to withstand supply transients up to 30 V.

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- [2] Measure according to DIN45004B;  $f_p$  = 540.25 MHz;  $V_p$  =  $V_o$ ;  $f_q$  = 547.25 MHz;  $V_q$  =  $V_o$  6 dB;  $f_r$  = 549.25 MHz;  $V_r$  =  $V_o$  6 dB; measured at  $f_p$  +  $f_q$   $f_r$  = 538.25 MHz.
- [3] The module normally operates at  $V_B = 24 \text{ V}$ , but is able to withstand supply transients up to 30 V.

**Table 8.** Characteristics Bandwidth 40 MHz to 450 MHz;  $V_B = 24$  V;  $T_{mb} = 35$  °C;  $Z_S = Z_L = 75 \Omega$ .

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$G_p$	power gain	f = 50 MHz		19.5	20	20.5	dB
		f = 450 MHz		20	20.6	-	dB
SL	slope cable equivalent	f = 40 MHz to 450 MHz		0	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 450 MHz		-	-	±0.3	dB
S <sub>11</sub>	input return losses	f = 40 MHz to 80 MHz		20	31	-	dB
		f = 80 MHz to 160 MHz		19	29	-	dB
		f = 160 MHz to 320 MHz		18	25	-	dB
		f = 320 MHz to 450 MHz		17	21	-	dB
S <sub>22</sub>	output return losses	f = 40 MHz to 80 MHz		20	26	-	dB
		f = 80 MHz to 160 MHz		19	27	-	dB
		f = 160 MHz to 320 MHz		18	26	-	dB
		f = 320 MHz to 450 MHz		17	24	-	dB
S <sub>21</sub>	phase response	f = 50 MHz		-45	-	+45	deg
СТВ	composite triple beat	60 channels flat; $V_o$ = 46 dBmV; measured at 445.25 MHz		-	-	-67	dB
$X_{mod}$	cross modulation	60 channels flat; $V_o = 46 \text{ dBmV}$ ; measured at 55.25 MHz		-	-	-64	dB
CSO	composite second order distortion	60 channels flat; $V_o$ = 46 dBmV; measured at 446.5 MHz		-	-	-63	dB
d <sub>2</sub>	second order distortion		[1]	-	-	-73	dB
$V_{o}$	output voltage	$d_{im} = -60 \text{ dB}$	[2]	66	-	-	dBmV
F	noise figure	see <u>Table 5</u>		-	-	-	dB
I <sub>tot</sub>	total current consumption (DC)		[3]	-	425	435	mA

<sup>[1]</sup>  $f_p$  = 55.25 MHz;  $V_p$  = 44 dBmV;  $f_q$  = 391.25 MHz;  $V_q$  = 46 dBmV; measured at  $f_p$  +  $f_q$  = 446.5 MHz.

<sup>[2]</sup> Measured according to DIN45004B;  $f_p = 440.25$  MHz;  $V_p = V_o$ ;  $f_q = 447.25$  MHz;  $V_q = V_o - 6$  dB;  $f_r = 449.25$  MHz;  $V_r = V_o - 6$  dB; measured at  $f_p + f_q - f_r = 438.25$  MHz.

<sup>[3]</sup> The module normally operates at  $V_B = 24 \text{ V}$ , but is able to withstand supply transients up to 30 V.

### 750 MHz, 20 dB gain power doubler amplifier

# 6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J

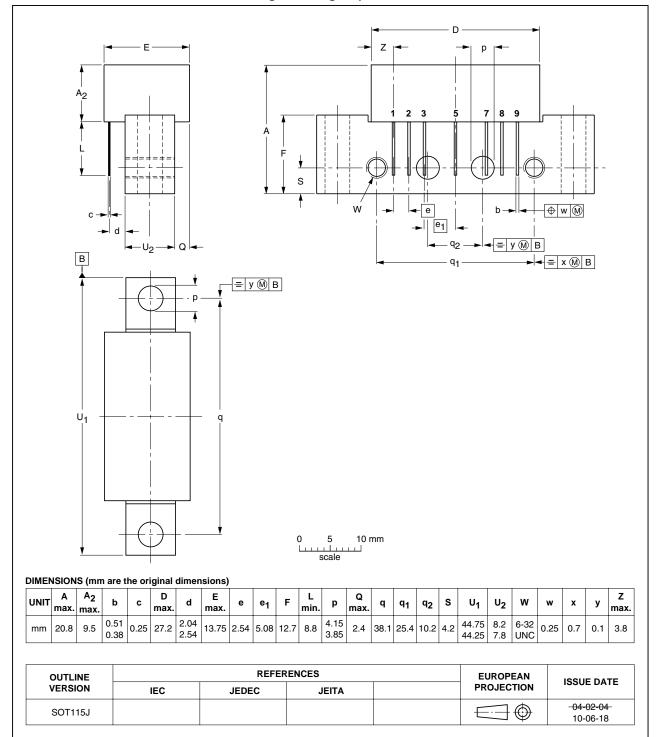


Fig 1. Package outline SOT115J

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**BGD704 NXP Semiconductors** 

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# **Revision history**

#### Table 9. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGD704 v.8	20100928	Product data sheet	-	BGD704 v.7
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity
	<ul> <li>Legal texts</li> </ul>	have been adapted to the ne	ew company name whe	ere appropriate.
	<ul> <li>Package ou</li> </ul>	ıtline drawings have been up	dated to the latest vers	sion.
BGD704 v.7 (9397 750 14776)	20050401	Product data sheet	-	BGD704 v.6
BGD704 v.6 (9397 750 09027)	20011102	Product specification	-	BGD704 v.5
BGD704 v.5 (9397 750 08846)	20011029	Product specification	-	BGD704 v.4
BGD704 v.4 (9397 750 05295)	19990322	Product specification	-	BGD704 v.3
BGD704 v.3 (9397 750 01971)	19970402	Product specification	-	BGD704 v.2
BGD704 v.2 (9397 750 01392)	19961220	Product specification	-	-

### 750 MHz, 20 dB gain power doubler amplifier

### 8. Legal information

#### 8.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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### 750 MHz, 20 dB gain power doubler amplifier

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

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В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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